

ABSTRACT

COMPOSITION FOR GAP FORMATION, AND SEMICONDUCTOR
DEVICE COMPRISING GAPS FORMED USING THE COMPOSITION,
AND METHOD FOR PRODUCING SEMICONDUCTOR DEVICE
USING THE COMPOSITION

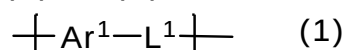
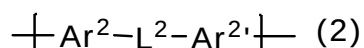
[Problem]

To provide a composition for gap formation capable of forming sacrifice areas made of a sacrificial material decomposable completely into vapor at a desired temperature, and also to provide a semiconductor device-manufacturing method using the composition.

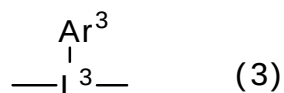
[Solution]

Disclosed is a composition for gap formation comprising a polymer and a solvent:

wherein said polymer comprising five or more of repeating units which are represented by at least one kind of the following formula (1) or (2):



[each of Ar^1 , Ar^2 and $\text{Ar}^{2'}$ is independently a substituted or unsubstituted aromatic group; and each of L^1 and L^2 is independently oxygen, sulfur, alkyl, sulfone, amide, ketone or a group represented by the following formula (3):



{ Ar^3 is an aromatic group; and L^3 is a trivalent atom selected from the group consisting of nitrogen, boron and phosphorus}}].

[Figure 1]